

62mm module with fast Trench/Fieldstop IGBT and Fast Recovery Diode

Features

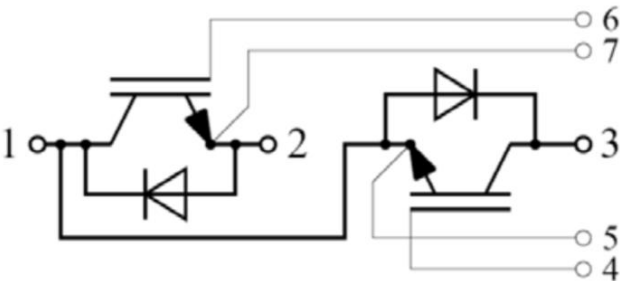
- 1200V 200A, $V_{CE(sat)}(typ.)=1.9V$
- High Short Circuit Capability, Self Limiting Short Circuit Current
- Trench+Field Stop Technology
- Low Switching Loss, Fast Switching
- Free Wheeling Diodes with Fast and Soft Reverse Recovery
- Positive Temperature Coefficient

Applications

- High Frequency Switching Application
- Medical Applications
- UPS Systems
- Motion Control, Servo Control



Equivalent Circuit Schematic



IGBT - Inverter
Maximum Rated Values

Symbol	Description	Conditions	Values	Unit
V_{CES}	Collector-Emitter Voltage	$T_{vj}=25^{\circ}C$	1200	V
V_{GES}	Gate-Emitter Peak Voltage	$T_{vj}=25^{\circ}C$	± 20	V
I_C	Continuous DC Collector Current	$T_C=100^{\circ}C$	200	A
I_{CRM}	Repetitive Peak Collector Current	$t_p=1ms$	400	A
P_{tot}	Total Power Dissipation	$T_C=25^{\circ}C, T_{vj\ max}=175^{\circ}C$	1400	W

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=200A, T_{vj}=25^{\circ}C$	---	1.9	2.35	V
		$V_{GE}=15V, I_C=200A, T_{vj}=125^{\circ}C$	---	2.1	---	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE}=V_{CE}, I_C=2mA$	5.0	---	6.5	V
I_{CES}	Collector-Emitter Cut-Off Current	$V_{CE}=1200V, V_{GE}=0V$	---	---	1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=15V, V_{CE}=0V$	---	---	500	nA
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	---	14.9	---	nF
C_{res}	Reverse Transfer Capacitance		---	0.68	---	nF
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V$ $V_{GE}=\pm 15V$ $I_C=200A$ $R_G=5\Omega$ Inductive Load $T_{vj}=25^{\circ}C$	---	437	---	ns
t_r	Turn-on Rise Time		---	75	---	ns
$t_{d(off)}$	Turn-off Delay Time		---	436	---	ns
t_f	Turn-off Fall Time		---	165	---	ns
E_{on}	Turn-on Switching Loss		---	10	---	mJ
E_{off}	Turn-off Switching Loss		---	15	---	mJ
I_{SC}	Short Circuit Data	$V_{GE}\leq 15V, V_{CC}=900V$ $t_p\leq 10\mu s, T_{vj}=125^{\circ}C$	---	1200	---	A
$T_{VJ OP}$	Virtual Junction Temperature	Under Switching	-40	---	150	$^{\circ}C$
R_{thJC}	Thermal Resistance, Junction to Case	Per IGBT	---	---	0.11	K/W

Diode - Inverter

Maximum Rated Values

Symbol	Description	Conditions	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25^{\circ}C$	1200	V
I_F	Continuous DC Forward Current		200	A
I_{FRM}	Repetitive Peak Collector Current	$t_p=1ms$	400	A

Characteristic Values

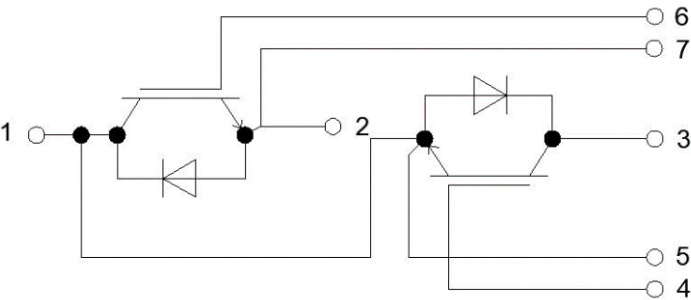
Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _F	Forward Voltage	I _F =200A, V _{GE} =0V, T _{vj} =25°C	---	1.8	2.25	V
		I _F =200A, V _{GE} =0V, T _{vj} =125°C	---	1.95	---	V
I _{rr}	Reverse Recovery Current	I _F =200A, V _R =600V, V _{GE} =-15V T _{vj} =125°C, di/dt=-2400A/us	---	210	---	A
Q _r	Recovered Charge		---	30	---	uC
E _{rec}	Reverse Recovery Energy		---	16	---	mJ
R _{thJC}	Thermal Resistance, Junction to Case	Per Diode	---	---	0.14	K/W

Module

Symbol	Description	Conditions	Values	Unit
V _{ISOL}	Isolation Test Voltage	RMS, f=50Hz, t=1min	3.0	KV

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
T _{stg}	Storage Temperature		-40	---	125	°C
M	Mounting Torque for Modul Mounting		3.0	---	5.0	Nm
G	Weight		---	302	---	g

Circuit Diagram



Package Outlines (mm)

